

John D Cressler

List of Publications by Citations

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275
papers

2,918
citations

25
h-index

35
g-index

297
ext. papers

3,615
ext. citations

2.1
avg, IF

5.25
L-index

#	Paper	IF	Citations
275	Radiation Effects in SiGe Technology. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 1992-2014	1.7	103
274	On the Analysis and Design of Low-Loss Single-Pole Double-Throw W-Band Switches Utilizing Saturated SiGe HBTs. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2014 , 62, 2755-2767	4.1	80
273	Multiple-Bit Upset in 130 nm CMOS Technology. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3259-3264	4.7	66
272	A 0.8 THz f_{MAX} SiGe HBT Operating at 4.3 K. <i>IEEE Electron Device Letters</i> , 2014 , 35, 151-153	4.4	47
271	A Silicon-Germanium Receiver for X-Band Transmit/Receive Radar Modules. <i>IEEE Journal of Solid-State Circuits</i> , 2008 , 43, 1889-1896	5.5	45
270	. <i>IEEE Transactions on Device and Materials Reliability</i> , 2010 , 10, 437-448	1.6	42
269	Sources of Phase Error and Design Considerations for Silicon-Based Monolithic High-Pass/Low-Pass Microwave Phase Shifters. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2006 , 54, 4032-4040	4.1	41
268	On the Performance Limits of Cryogenically Operated SiGe HBTs and Its Relation to Scaling for Terahertz Speeds. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 1007-1019	2.9	37
267	Substrate Engineering Concepts to Mitigate Charge Collection in Deep Trench Isolation Technologies. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3298-3305	1.7	35
266	An Investigation of Dose Rate and Source Dependent Effects in 200 GHz SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3166-3174	1.7	35
265	Application of RHBD Techniques to SEU Hardening of Third-Generation SiGe HBT Logic Circuits. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3400-3407	1.7	33
264	The Effects of Irradiation Temperature on the Proton Response of SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3175-3181	1.7	32
263	A New Self-Healing Methodology for RF Amplifier Circuits Based on Oscillation Principles. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2012 , 20, 1835-1848	2.6	31
262	Reliability of SiGe HBTs for Power Amplifiers Part I: Large-Signal RF Performance and Operating Limits. <i>IEEE Transactions on Device and Materials Reliability</i> , 2009 , 9, 431-439	1.6	31
261	Heavy Ion Microbeam- and Broadbeam-Induced Transients in SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3078-3084	1.7	31
260	A Comparison of the Degradation in RF Performance Due to Device Interconnects in Advanced SiGe HBT and CMOS Technologies. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 1803-1810	2.9	30
259	Sub-1-K Operation of SiGe Transistors and Circuits. <i>IEEE Electron Device Letters</i> , 2009 , 30, 508-510	4.4	30

258	An Evaluation of Transistor-Layout RHBD Techniques for SEE Mitigation in SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 2044-2052	1.7	30
257	Laser-Induced Current Transients in Silicon-Germanium HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 2936-2942	1.7	29
256	Design and Analysis of a Low Loss, Wideband Digital Step Attenuator With Minimized Amplitude and Phase Variations. <i>IEEE Journal of Solid-State Circuits</i> , 2018 , 53, 2202-2213	5.5	28
255	Predictive Physics-Based TCAD Modeling of the Mixed-Mode Degradation Mechanism in SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 2895-2901	2.9	28
254	Design of Radiation-Hardened RF Low-Noise Amplifiers Using Inverse-Mode SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 3218-3225	1.7	26
253	The effects of operating bias conditions on the proton tolerance of SiGe HBTs. <i>Solid-State Electronics</i> , 2003 , 47, 1729-1734	1.7	26
252	A 94 GHz, 1.4 dB Insertion Loss Single-Pole Double-Throw Switch Using Reverse-Saturated SiGe HBTs. <i>IEEE Microwave and Wireless Components Letters</i> , 2014 , 24, 56-58	2.6	25
251	An 816 GHz SiGe Low Noise Amplifier With Performance Tuning Capability for Mitigation of Radiation-Induced Performance Loss. <i>IEEE Transactions on Nuclear Science</i> , 2012 , 59, 2837-2846	1.7	25
250	A Low-Loss and High Isolation D-Band SPDT Switch Utilizing Deep-Saturated SiGe HBTs. <i>IEEE Microwave and Wireless Components Letters</i> , 2014 , 24, 400-402	2.6	24
249	CMOS reliability issues for emerging cryogenic Lunar electronics applications. <i>Solid-State Electronics</i> , 2006 , 50, 959-963	1.7	23
248	. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3469-3476	1.7	22
247	Reliability of SiGe HBTs for Power Amplifiers Part II: Underlying Physics and Damage Modeling. <i>IEEE Transactions on Device and Materials Reliability</i> , 2009 , 9, 440-448	1.6	22
246	A Generalized SiGe HBT Single-Event Effects Model for On-Orbit Event Rate Calculations. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 2322-2329	1.7	22
245	Proton and gamma radiation effects in a new first-generation SiGe HBT technology. <i>Solid-State Electronics</i> , 2006 , 50, 181-190	1.7	22
244	A Lightweight Organic X-Band Active Receiving Phased Array With Integrated SiGe Amplifiers and Phase Shifters. <i>IEEE Transactions on Antennas and Propagation</i> , 2011 , 59, 100-109	4.9	21
243	Single Event Upset Mechanisms for Low-Energy-Deposition Events in SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 1581-1586	1.7	21
242	Using TCAD Modeling to Compare Heavy-Ion and Laser-Induced Single Event Transients in SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2017 , 64, 398-405	1.7	20
241	. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 1383-1389	2.9	20

240	A Class-E Tuned W-Band SiGe Power Amplifier With 40.4% Power-Added Efficiency at 93 GHz. <i>IEEE Microwave and Wireless Components Letters</i> , 2015 , 25, 663-665	2.6	20
239	SiGe HBT X-Band LNAs for Ultra-Low-Noise Cryogenic Receivers. <i>IEEE Microwave and Wireless Components Letters</i> , 2008 , 18, 476-478	2.6	20
238	Temperature-Dependence of Off-State Drain Leakage in X-Ray Irradiated 130 nm CMOS Devices. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3203-3209	1.7	20
237	Application of a Pelletron accelerator to study total dose radiation effects on 50 GHz SiGe HBTs. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012 , 273, 43-46	1.2	19
236	Design of Digital Circuits Using Inverse-Mode Cascode SiGe HBTs for Single Event Upset Mitigation. <i>IEEE Transactions on Nuclear Science</i> , 2010 ,	1.7	19
235	3-D Simulation of SEU Hardening of SiGe HBTs Using Shared Dummy Collector. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 2330-2337	1.7	19
234	Proton Tolerance of SiGe Precision Voltage References for Extreme Temperature Range Electronics. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3210-3216	1.7	19
233	Operation of SiGe HBTs Down to 70 mK. <i>IEEE Electron Device Letters</i> , 2017 , 38, 12-15	4.4	18
232	Experimental Validation of an Equivalent LET Approach for Correlating Heavy-Ion and Laser-Induced Charge Deposition. <i>IEEE Transactions on Nuclear Science</i> , 2018 , 65, 1724-1733	1.7	18
231	. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3393-3401	1.7	18
230	Single-Event Response of the SiGe HBT Operating in Inverse-Mode. <i>IEEE Transactions on Nuclear Science</i> , 2012 , 59, 2682-2690	1.7	17
229	An Investigation of Single-Event Effects and Potential SEU Mitigation Strategies in Fourth-Generation, 90 nm SiGe BiCMOS. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 4175-4183	1.7	17
228	Reconciling 3-D Mixed-Mode Simulations and Measured Single-Event Transients in SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2010 , 57, 3342-3348	1.7	17
227	Compact Modeling of Mutual Thermal Coupling for the Optimal Design of SiGe HBT Power Amplifiers. <i>IEEE Transactions on Electron Devices</i> , 2009 ,	2.9	17
226	Application of advanced 200 GHz SiGe HBTs for high dose radiation environments. <i>Solid-State Electronics</i> , 2010 , 54, 1554-1560	1.7	17
225	A 2 mW, Sub-2 dB Noise Figure, SiGe Low-Noise Amplifier For X-band High-Altitude or Space-based Radar Applications. <i>Radio Frequency Integrated Circuits (RFIC) Symposium, IEEE</i> , 2007 ,		17
224	. <i>IEEE Transactions on Nuclear Science</i> , 2017 , 64, 406-414	1.7	16
223	A SiGe D-Band Low-Noise Amplifier Utilizing Gain-Boosting Technique. <i>IEEE Microwave and Wireless Components Letters</i> , 2015 , 25, 61-63	2.6	16

222	Trade-Offs Between RF Performance and Total-Dose Tolerance in 45-nm RF-CMOS. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 2830-2837	1.7	16
221	The Enhanced Role of Shallow-Trench Isolation in Ionizing Radiation Damage of 65 nm RF-CMOS on SOI. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3256-3261	1.7	16
220	On the Frequency Limits of SiGe HBTs for TeraHertz Applications. <i>Bipolar/BiCMOS Circuits and Technology Meeting, IEEE Proceedings of the</i> , 2007 ,		16
219	Impact of Scaling on the Inverse-Mode Operation of SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 1492-1501	2.9	16
218	The Effects of Scaling and Bias Configuration on Operating-Voltage Constraints in SiGe HBTs for Mixed-Signal Circuits. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 1605-1616	2.9	16
217	Advanced SiGe BiCMOS Technology for Multi-Mrad Electronic Systems. <i>IEEE Transactions on Device and Materials Reliability</i> , 2014 , 14, 844-848	1.6	15
216	Reliability studies on NPN RF power transistors under swift heavy ion irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012 , 273, 36-39	1.2	15
215	Total Dose and Transient Response of SiGe HBTs from a New 4th-Generation, 90 nm SiGe BiCMOS Technology 2012 ,		15
214	Optimizing Inverse-Mode SiGe HBTs for Immunity to Heavy-Ion-Induced Single-Event Upset. <i>IEEE Electron Device Letters</i> , 2009 , 30, 511-513	4.4	15
213	The Effects of Proton and X-Ray Irradiation on the DC and AC Performance of Complementary (npn + pnp) SiGe HBTs on Thick-Film SOI. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 2245-2250	1.7	15
212	2007 ,		15
211	Design and On-Wafer Characterization of $\$G\$$ -Band SiGe HBT Low-Noise Amplifiers. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2016 , 64, 3631-3642	4.1	15
210	A True Time Delay-based SiGe Bi-directional T/R Chipset for Large-Scale Wideband Timed Array Antennas 2018 ,		14
209	Single-Event Transient and Total Dose Response of Precision Voltage Reference Circuits Designed in a 90-nm SiGe BiCMOS Technology. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 3210-3217	1.7	14
208	A 60 GHz Adaptive SiGe Image Reject Mixer for a Self-Healing Receiver. <i>IEEE Journal of Solid-State Circuits</i> , 2012 , 47, 1998-2006	5.5	14
207	The Effects of X-Ray and Proton Irradiation on a 200 GHz/90 GHz Complementary $\$(nnp + pnp)\$$ SiGe:C HBT Technology. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 2190-2195	1.7	14
206	Optimizing Optical Parameters to Facilitate Correlation of Laser- and Heavy-Ion-Induced Single-Event Transients in SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2019 , 66, 359-367	1.7	14
205	Bias- and Temperature-Dependent Accumulated Stress Modeling of Mixed-Mode Damage in SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2084-2091	2.9	13

204	Impact of Technology Scaling in sub-100 nm nMOSFETs on Total-Dose Radiation Response and Hot-Carrier Reliability. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 1426-1432	1.7	13
203	2014 ,		13
202	An Investigation of Single Event Transient Response in 45-nm and 32-nm SOI RF-CMOS Devices and Circuits. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 4405-4411	1.7	13
201	A Theory of Single-Event Transient Response in Cross-Coupled Negative Resistance Oscillators. <i>IEEE Transactions on Nuclear Science</i> , 2010 ,	1.7	13
200	50 MeV Li ³⁺ ion irradiation effects on advanced 200 GHz SiGe HBTs. <i>Radiation Effects and Defects in Solids</i> , 2011 , 166, 710-717	0.9	13
199	On CommonBase Avalanche Instabilities in SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1276-1285	2.9	13
198	A Physics-Based Circuit Aging Model for Mixed-Mode Degradation in SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2987-2993	2.9	12
197	Potential Limitations on Integrated Silicon Photonic Waveguides Operating in a Heavy Ion Environment. <i>IEEE Transactions on Nuclear Science</i> , 2018 , 65, 141-148	1.7	12
196	An investigation of electron and oxygen ion damage in Si npn RF power transistors. <i>Radiation Effects and Defects in Solids</i> , 2009 , 164, 592-603	0.9	12
195	A 12-Bit Cryogenic and Radiation-Tolerant Digital-to-Analog Converter for Aerospace Extreme Environment Applications. <i>IEEE Transactions on Industrial Electronics</i> , 2008 , 55, 2810-2819	8.9	12
194	A Comparison of the Effects of X-Ray and Proton Irradiation on the Performance of SiGe Precision Voltage References. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 2238-2244	1.7	12
193	The Application of RHBD to n-MOSFETs Intended for Use in Cryogenic-Temperature Radiation Environments. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 2100-2105	1.7	12
192	SiGe BiCMOS Precision Voltage References for Extreme Temperature Range Electronics 2006 ,		12
191	New Approach for Pulsed-Laser Testing That Mimics Heavy-Ion Charge Deposition Profiles. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 81-90	1.7	12
190	A Comparison of Field and Current-Driven Hot-Carrier Reliability in NPN SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2244-2250	2.9	11
189	An Investigation of Single-Event Transients in C-SiGe HBT on SOI Current Mirror Circuits. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 3193-3200	1.7	11
188	Evaluation of Enhanced Low Dose Rate Sensitivity in Fourth-Generation SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 2915-2922	1.7	11
187	On the Transient Response of a Complementary (nnp $\bar{+}+$ pnp) SiGe HBT BiCMOS Technology. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 3146-3153	1.7	11

186	A 1.0 V, 1002 GHz, 4 mW LNA Utilizing Weakly Saturated SiGe HBTs for Single-Chip, Low-Power, Remote Sensing Applications. <i>IEEE Microwave and Wireless Components Letters</i> , 2014 , 24, 890-892	2.6	11
185	A new approach to designing electronic systems for operation in extreme environments: Part I - The SiGe Remote Sensor Interface. <i>IEEE Aerospace and Electronic Systems Magazine</i> , 2012 , 27, 25-34	2.4	11
184	2012 ,		11
183	Total Ionizing Dose Response of Triple-Well FET-Based Wideband, High-Isolation RF Switches in a 130 nm SiGe BiCMOS Technology. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 2567-2573	1.7	11
182	Design and Optimization of Superjunction Collectors for Use in High-Speed SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 1655-1662	2.9	11
181	On the RF Properties of Weakly Saturated SiGe HBTs and Their Potential Use in Ultralow-Voltage Circuits. <i>IEEE Electron Device Letters</i> , 2011 , 32, 3-5	4.4	11
180	SiGe HBT compact modeling for extreme temperatures 2007 ,		11
179	SEU Error Signature Analysis of Gbit/s SiGe Logic Circuits Using a Pulsed Laser Microprobe. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3277-3284	1.7	11
178	A New Current-Sweep Method for Assessing the Mixed-Mode Damage Spectrum of SiGe HBTs. <i>IEEE Transactions on Device and Materials Reliability</i> , 2007 , 7, 479-487	1.6	11
177	Addressing challenges in device-circuit modeling for extreme environments of space 2007 ,		11
176	X-Ray Irradiation and Bias Effects in Fully-Depleted and Partially-Depleted SiGe HBTs Fabricated on CMOS-Compatible SOI. <i>IEEE Transactions on Nuclear Science</i> , 2006 , 53, 3182-3186	1.7	11
175	A High-Slew Rate SiGe BiCMOS Operational Amplifier for Operation Down to Deep Cryogenic Temperatures. <i>Bipolar/BiCMOS Circuits and Technology Meeting, IEEE Proceedings of the</i> , 2006 ,		11
174	Silicon bipolar transistor: a viable candidate for high speed applications at liquid nitrogen temperature. <i>Cryogenics</i> , 1990 , 30, 1036-1047	1.8	11
173	A 60-GHz SiGe Radiometer Calibration Switch Utilizing a Coupled Avalanche Noise Source. <i>IEEE Microwave and Wireless Components Letters</i> , 2020 , 30, 417-420	2.6	11
172	An Investigation of the Use of Inverse-Mode SiGe HBTs as Switching Pairs for SET-Mitigated RF Mixers. <i>IEEE Transactions on Nuclear Science</i> , 2016 , 63, 1099-1108	1.7	11
171	A 0.3-5 GHz SiGe LNA With >1 THz Gain-Bandwidth Product. <i>IEEE Microwave and Wireless Components Letters</i> , 2017 , 27, 380-382	2.6	10
170	Total Ionizing Dose Effects in 70-GHz Bandwidth Photodiodes in a SiGe Integrated Photonics Platform. <i>IEEE Transactions on Nuclear Science</i> , 2019 , 66, 125-133	1.7	10
169	Accurate Modeling of Single-Event Transients in a SiGe Voltage Reference Circuit. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 877-884	1.7	10

168	Compact Modeling of the Temperature Dependence of Parasitic Resistances in SiGe HBTs Down to 30 K. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2169-2177	2.9	10
167	3-D Mixed-Mode Simulation of Single Event Transients in SiGe HBT Emitter Followers and Resultant Hardening Guidelines. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 3360-3366	1.7	10
166	Analysis and understanding of unique cryogenic phenomena in state-of-the-art SiGe HBTs. <i>Solid-State Electronics</i> , 2006 , 50, 964-972	1.7	10
165	A SiGe-BiCMOS Wideband (202 GHz) Active Power Divider/Combiner Circuit Supporting Bidirectional Operation. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2016 , 64, 4676-4684	4.1	10
164	A Compact, Wideband Lumped-Element Wilkinson Power Divider/Combiner Using Symmetric Inductors with Embedded Capacitors. <i>IEEE Microwave and Wireless Components Letters</i> , 2016 , 26, 595-597 ^{2.6}	2.6	10
163	A Compact Highly Efficient High-Power Ka-band SiGe HBT Cascode Frequency Doubler With Four-Way Input Transformer Balun. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2018 , 66, 2879-2887	4.1	9
162	An Active Bi-Directional SiGe DPDT Switch With Multi-Octave Bandwidth. <i>IEEE Microwave and Wireless Components Letters</i> , 2016 , 26, 279-281	2.6	9
161	An Investigation of Single-Event Effect Modeling Techniques for a SiGe RF Low-Noise Amplifier. <i>IEEE Transactions on Nuclear Science</i> , 2016 , 63, 273-280	1.7	9
160	Collector Transport in SiGe HBTs Operating at Cryogenic Temperatures. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 3697-3703	2.9	9
159	. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 756-765	1.7	9
158	Establishing Best-Practice Modeling Approaches for Understanding Single-Event Transients in Gb/s SiGe Digital Logic. <i>IEEE Transactions on Nuclear Science</i> , 2012 , 59, 958-964	1.7	9
157	. <i>IEEE Transactions on Nuclear Science</i> , 2010 ,	1.7	9
156	Impact of deep trench isolation on advanced SiGe HBT reliability in radiation environments 2009 ,		9
155	A New Analytical Method for Robust Extraction of the Small-Signal Equivalent Circuit for SiGe HBTs Operating at Cryogenic Temperatures. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2008 , 56, 568-574	4.1	9
154	Applications of heavy ion microprobe for single event effects analysis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 261, 443-446	1.2	9
153	A High-Linearity 5-bit, X-band SiGe HBT Phase Shifter 2006 ,		9
152	The Effects of Proton Irradiation on 90 nm Strained Si CMOS on SOI Devices 2006 ,		9
151	Proton response of low-frequency noise in 0.20 μ m 90 GHz FT UHV/CVD SiGe HBTs. <i>Solid-State Electronics</i> , 2003 , 47, 39-44	1.7	9

150	A SiGe 80-GHz Receiver With Built-In-Testing Capability for Self-Healing Applications. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2014 , 62, 2370-2380	4.1	8
149	Single-Event Effects in a W-Band (75-110 GHz) Radar Down-Conversion Mixer Implemented in 90 nm, 300 GHz SiGe HBT Technology. <i>IEEE Transactions on Nuclear Science</i> , 2015 , 62, 2657-2665	1.7	8
148	Impact of Total Ionizing Dose on a 4th Generation, 90 nm SiGe HBT Gaussian Pulse Generator. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 3050-3054	1.7	8
147	W-band SiGe power amplifiers 2014 ,		8
146	A compact, transformer-based 60 GHz SPDT RF switch utilizing diode-connected SiGe HBTs 2013 ,		8
145	An Investigation of DC and RF Safe Operating Area of n-p-n \pm p-n-p SiGe HBTs on SOI. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 2573-2581	2.9	8
144	Influence of Interface Traps on the Temperature Sensitivity of MOSFET Drain-Current Variations. <i>IEEE Electron Device Letters</i> , 2010 , 31, 387-389	4.4	8
143	A monolithic, wide-temperature, charge amplification channel for extreme environments 2010 ,		8
142	Re-Examining TID Hardness Assurance Test Protocols for SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3318-3325	1.7	8
141	An Investigation of Negative Differential Resistance and Novel Collector Current Kink Effects in SiGe HBTs Operating at Cryogenic Temperatures. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 504-516	2.9	8
140	Proton-induced SEU in SiGe digital logic at cryogenic temperatures. <i>Solid-State Electronics</i> , 2008 , 52, 1652-1659	1.7	8
139	Understanding Radiation- and Hot Carrier-Induced Damage Processes in SiGe HBTs Using Mixed-Mode Electrical Stress. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 1938-1945	1.7	8
138	Highly Linear High-Power 802.11ac/ax WLAN SiGe HBT Power Amplifiers With a Compact 2nd-Harmonic-Shorted Four-Way Transformer and a Thermally Compensating Dynamic Bias Circuit. <i>IEEE Journal of Solid-State Circuits</i> , 2020 , 55, 2356-2370	5.5	8
137	Optical Single-Event Transients Induced in Integrated Silicon-Photonic Waveguides by Two-Photon Absorption. <i>IEEE Transactions on Nuclear Science</i> , 2021 , 68, 785-792	1.7	8
136	A Low-Loss Broadband Quadrature Signal Generation Network for High Image Rejection at Millimeter-Wave Frequencies. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2018 , 66, 5336-5346	4.1	8
135	On the Application of Inverse-Mode SiGe HBTs in RF Receivers for the Mitigation of Single-Event Transients. <i>IEEE Transactions on Nuclear Science</i> , 2017 , 64, 1142-1150	1.7	7
134	Physical Differences in Hot Carrier Degradation of Oxide Interfaces in Complementary (n-p-n+p-n-p) SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 37-44	2.9	7
133	Hot-Carrier-Damage-Induced Current Gain Enhancement (CGE) Effects in SiGe HBTs. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2430-2438	2.9	7

132	Single-Event Transient Response of Comparator Pre-Amplifiers in a Complementary SiGe Technology. <i>IEEE Transactions on Nuclear Science</i> , 2017 , 64, 89-96	1.7	7
131	Optimization of SiGe HBT RF Switches for Single-Event Transient Mitigation. <i>IEEE Transactions on Nuclear Science</i> , 2015 , 62, 3057-3063	1.7	7
130	An Ultra-Thin, High-Power, and Multilayer Organic Antenna Array With T/R Functionality in the X-Band. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2012 , 60, 3856-3867	4.1	7
129	A Mechanism Versus SEU Impact Analysis of Collector Charge Collection in SiGe HBT Current Mode Logic. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3071-3077	1.7	7
128	Novel Total Dose and Heavy-Ion Charge Collection Phenomena in a New SiGe HBT on μ Thin-Film SOI Technology. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 3197-3201	1.7	7
127	Using Bessel beams and two-photon absorption to predict radiation effects in microelectronics. <i>Optics Express</i> , 2019 , 27, 37652-37666	3.3	7
126	A New Wideband, Low Insertion Loss, High Linearity SiGe RF Switch. <i>IEEE Microwave and Wireless Components Letters</i> , 2020 , 30, 985-988	2.6	7
125	. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2018 , 66, 3866-3876	4.1	7
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